

Rev.E Mar.-2016

TO-3P

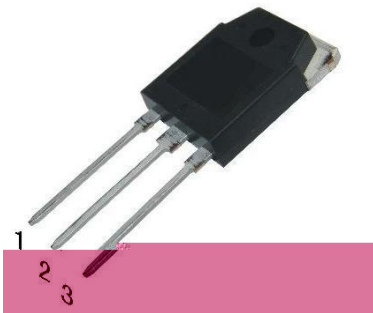
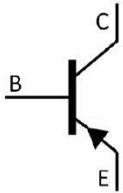
PNP

Silicon PNP transistor in a TO-3P Plastic Package.

TIP35C

Low leakage current, high current gain bandwidth product, Complementary to TIP35C.

Amplifier and switching applications.

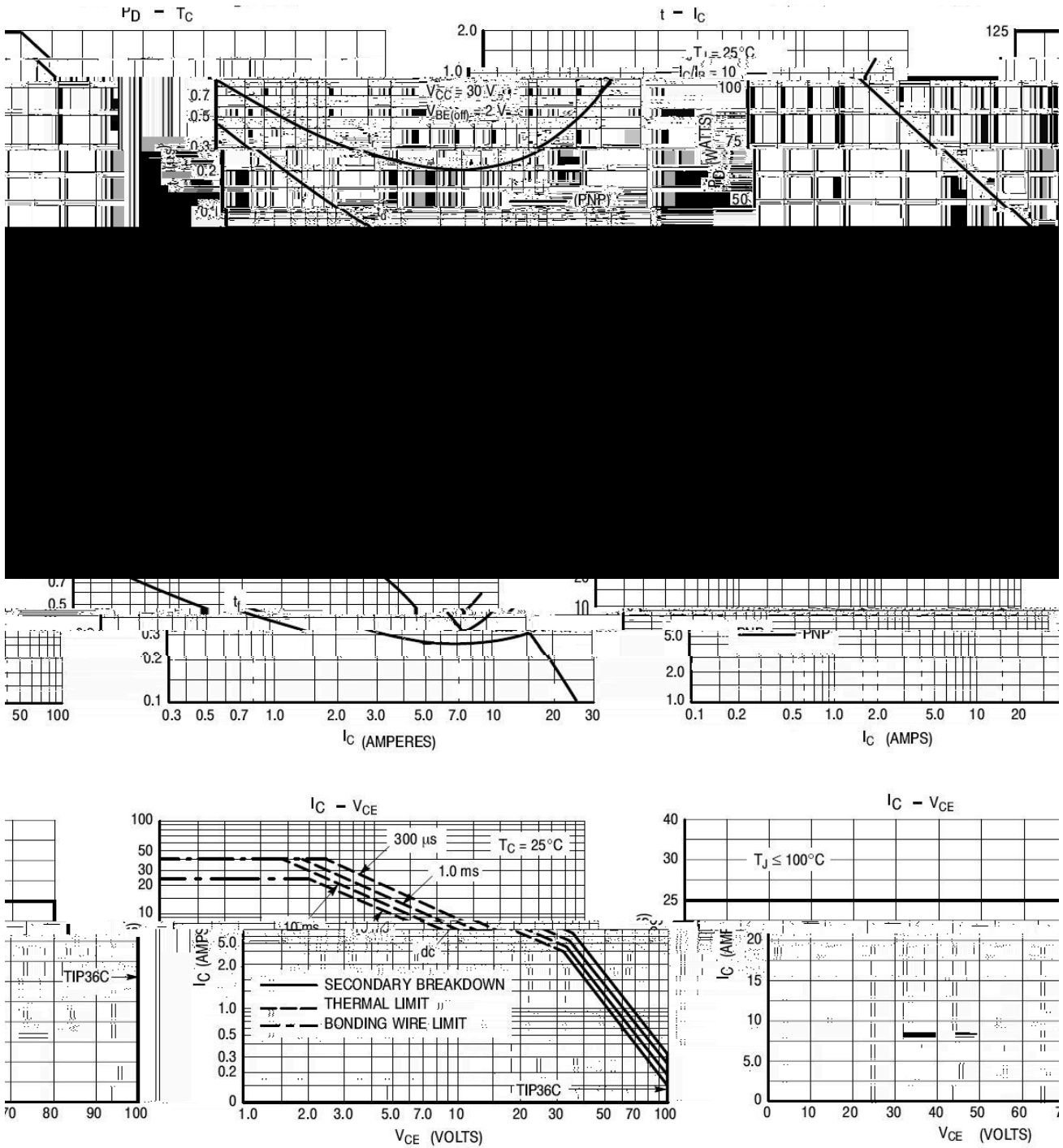


PIN1 Base PIN 2 Collector PIN 3 Emitter

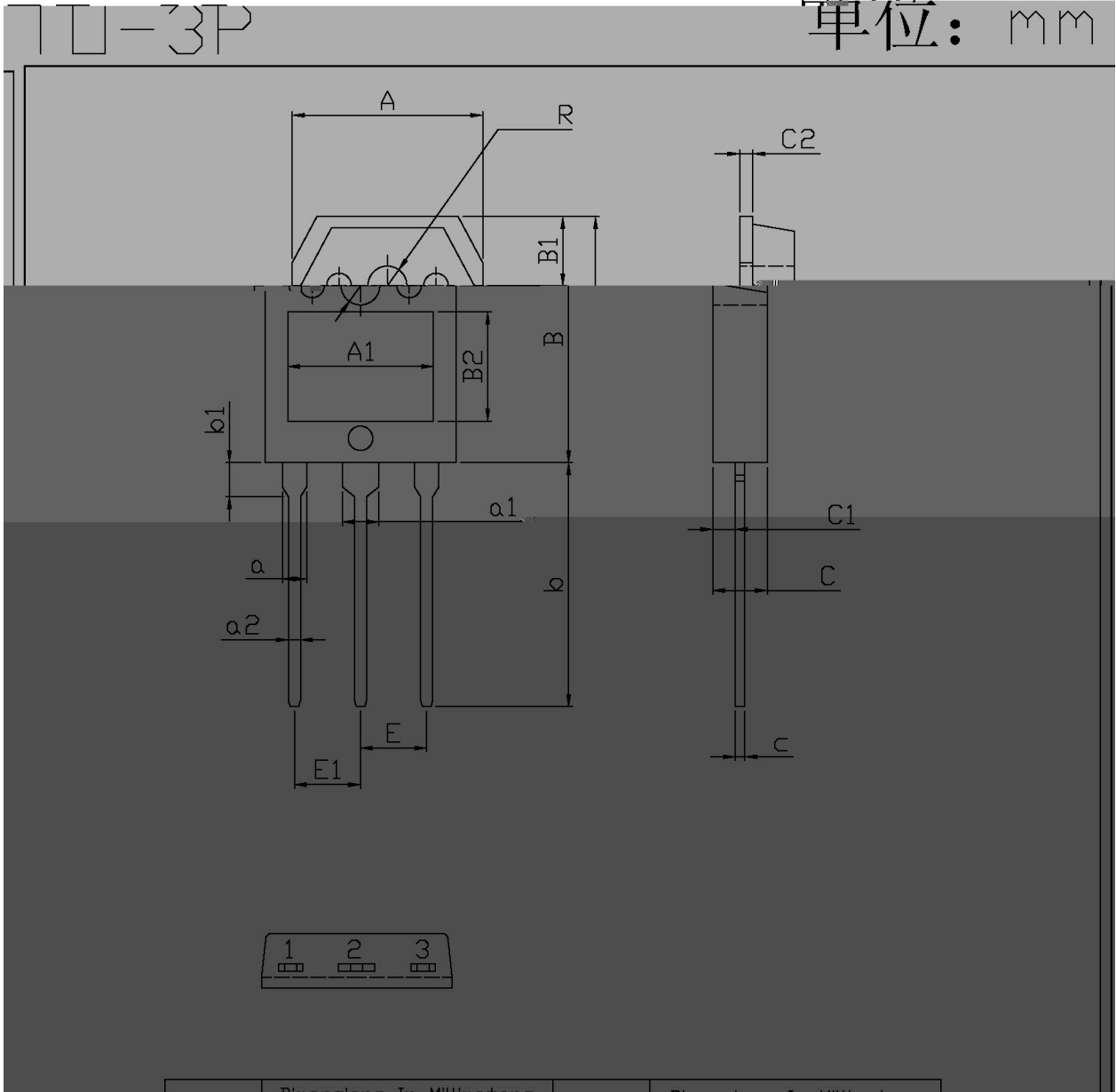
See Marking Instructions.

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-100	V
Collector to Emitter Voltage	V_{CEO}	-100	V
Emitter to Base Voltage	V_{EBO}	-5	V
Collector Current - Continuous	I_C	-25	A
Peak Collector Current	I_{CM}	-50	A
Base Current	I_B	-5	A
Total Power Dissipation	P_{tot}	125	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-65~150	
Thermal Resistance Junction	R_{thj}	1	/W

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cut-Off Current	I_{CEO}	$V_{CE}=-60V$ $I_B=0$			-1	mA
Collector Cut-Off Current	I_{CES}	$V_{CE}=-60V$ $V_{BE}=0$			-0.7	mA
Emitter Cut-Off Current	I_{EBO}	$V_{EB}=-5V$ $I_C=0$			-1	mA
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C=-30mA$ $I_B=0$	-100			V
DC Current Gain	$h_{FE(1)}$	$V_{CE}=-4V$ $I_C=-1.5A$	20		80	
	$h_{FE(2)}$	$V_{CE}=-4V$ $I_C=-15A$	15			
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=-15A$ $I_B=-1.5A$			-1.8	V
		$I_C=-25A$ $I_B=-5A$			-4	V
Base to Emitter Voltage	V_{BE}	$I_C=-15A$ $V_{CE}=-4V$			-2	V
		$V_{CE}=-4V$ $I_C=-25A$			-4	V
Transition Frequency	f_T	$V_{CE}=-10V$ $f=1MHz$ $I_C=-1A$	3			MHz



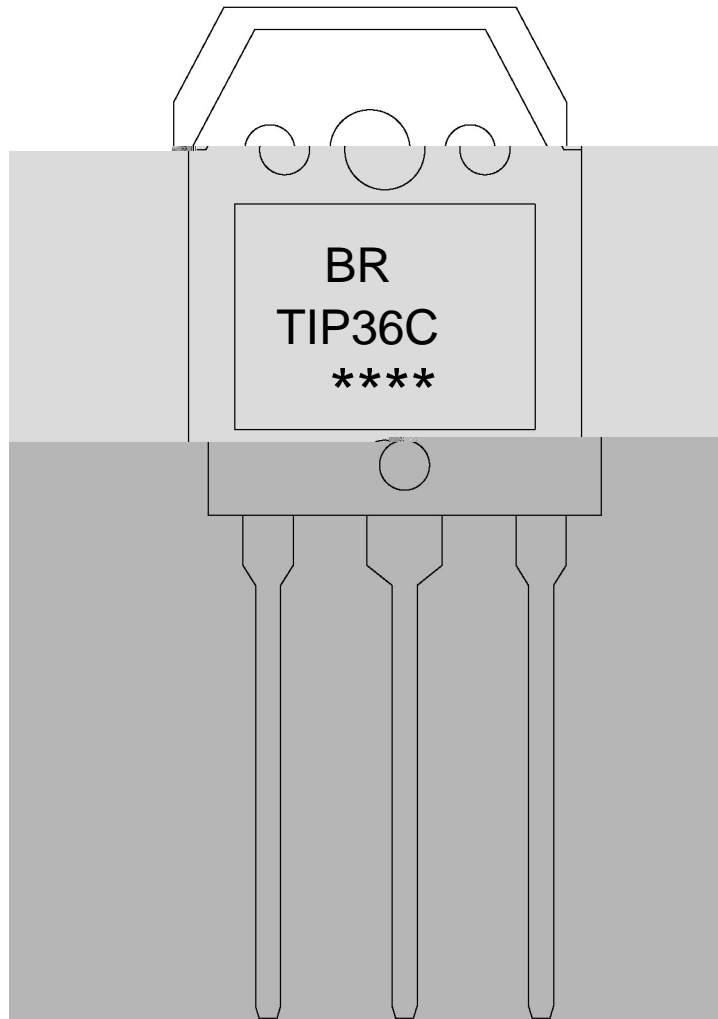
单位: mm



Dimensiones en Milímetros Dimensiones en Milímetros

Symbol

Symbol



BR:

TIP36C

Note:

BR: Company Code.

TIP36C: Product Type.

****: Lot No. Code, code change with Lot No.

Rev.E Mar.-2016